

ASYNCHRONOUS BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY

SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

- Independent Asynchronous Inputs and Outputs
- Low-Power Advanced CMOS Technology
- Bidirectional
- Dual 1024 by 9 Bits
- Programmable Almost-Full/Almost-Empty Flag
- Empty, Full, and Half-Full Flags
- Access Times of 25 ns With a 50-pF Load
- Data Rates up to 50 MHz
- Fall-Through Times of 22 ns Maximum
- High Output Drive for Direct Bus Interface
- Package Options Include 44-Pin Plastic Leaded Chip Carriers (FN) and 64-Pin Thin Quad Flat (PAG, PM) Packages

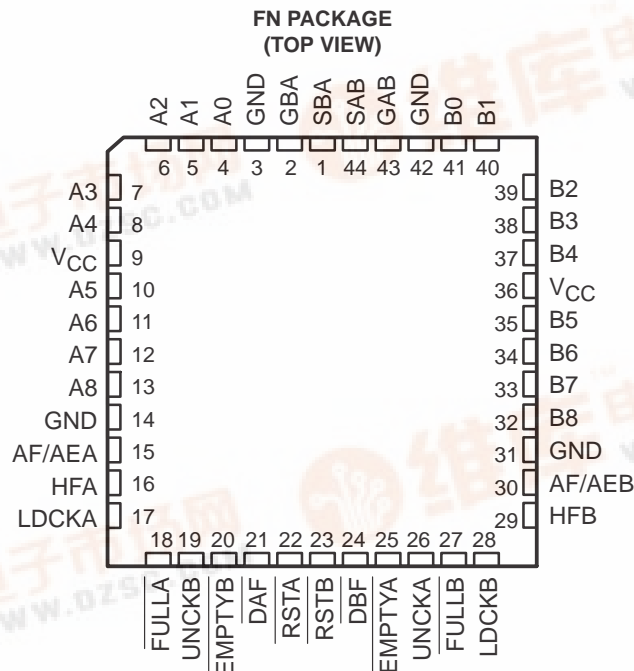
description

A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ACT2235 is arranged as two 1024 by 9-bit FIFOs for high speed and fast access times. It processes data at rates up to 50 MHz, with access times of 25 ns in a bit-parallel format.

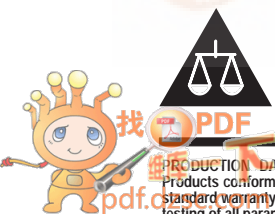
The SN74ACT2235 consists of bus-transceiver circuits, two 1024 × 9 FIFOs, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal FIFO memories. Enable (GAB and GBA) inputs are provided to control the transceiver functions. The select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 2 shows the eight fundamental bus-management functions that can be performed with the SN74ACT2235.

For more information on this device family, see the application report, *1K × 9 × 2 Asynchronous FIFO SN74ACT2235*, literature number SCAA010.

The SN74ACT2235 is characterized for operation from 0°C to 70°C.



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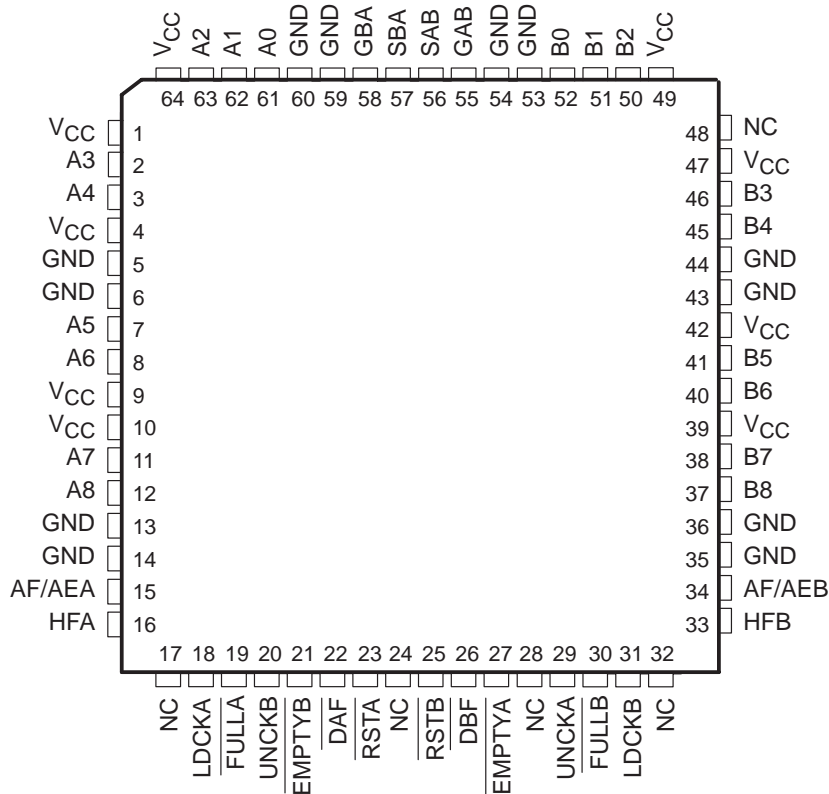
SN74ACT2235

1024 × 9 × 2

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SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

PAG OR PM PACKAGE
(TOP VIEW)



NC – No internal connection

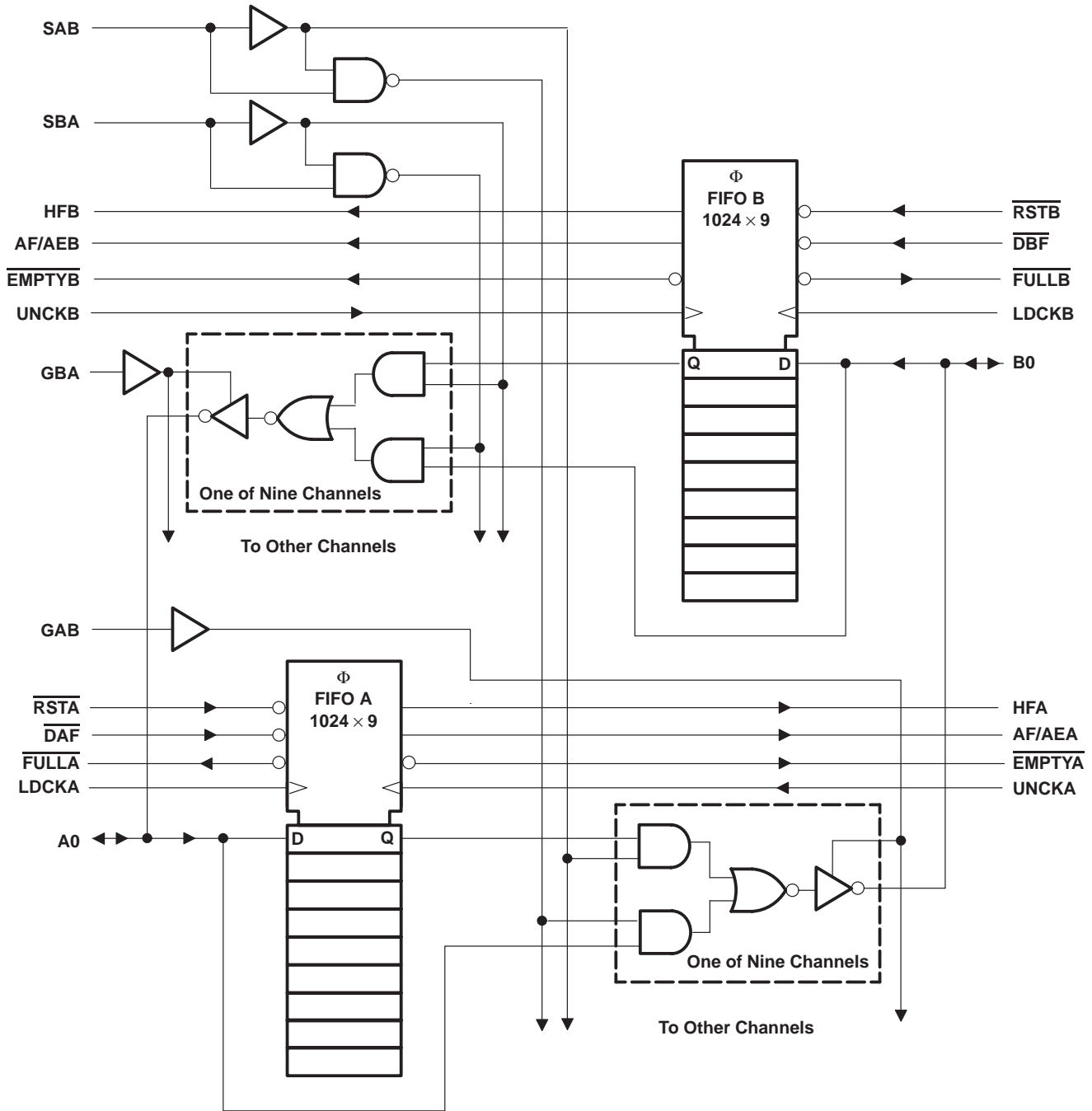
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logic diagram (positive logic)



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SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

Terminal Functions

TERMINAL† NAME	NO.	I/O	DESCRIPTION
AF/AEA AF/AEB	15 30	O	Almost full/almost empty flags. The almost-full/almost-empty A flag (AF/AEA) is defined by the almost-full/almost-empty offset value for FIFO A (X). AF/AEA is high when FIFO A contains X or fewer words or 1024–X words. AF/AEA is low when FIFO A contains between (X + 1) or (1023 – X) words. The operation of the almost-full/almost-empty B flag (AF/AEB) is the same as AF/AEA for FIFO B.
A0–A8	4–8, 10–13	I/O	A-data inputs and outputs
B0–B8	32–35, 37–41	I/O	B-data inputs and outputs
$\overline{\text{DAF}}$ DBF	21 24	I	Define-flag inputs. The high-to-low transition of $\overline{\text{DAF}}$ stores the binary value on A0–A8 as the almost-full/almost-empty offset value for FIFO A (X). The high-to-low transition of DBF stores the binary value of B0–B8 as the almost-full/almost-empty offset value for FIFO B (Y).
$\overline{\text{EMPTYA}}$ EMPTYB	20 25	O	Empty flags. $\overline{\text{EMPTYA}}$ and $\overline{\text{EMPTYB}}$ are low when their corresponding memories are empty and high when they are not empty.
$\overline{\text{FULLA}}$ FULLB	18 27	O	Full flags. $\overline{\text{FULLA}}$ and $\overline{\text{FULLB}}$ are low when their corresponding memories are full and high when they are not full.
HFA HFB	16 29	O	Half-full flags. HFA and HFB are high when their corresponding memories contain 512 or more words and low when they contain 511 or fewer words.
LDCKA LDCKB	17 28	I	Load clocks. Data on A0–A8 is written into FIFO A on a low-to-high transition of LDCKA. Data on B0–B8 is written into FIFO B on a low-to-high transition of LDCKB. When the FIFOs are full, LDCKA and LDCKB have no effect on the data residing in memory.
GAB GBA	2 43	I	Output enables. GAB, GBA control the transceiver functions. When GBA is low, A0–A8 are in the high-impedance state. When GAB is low, B0–B8 are in the high-impedance state.
$\overline{\text{RSTA}}$ $\overline{\text{RSTB}}$	22 23	I	Reset. A reset is accomplished in each direction by taking $\overline{\text{RSTA}}$ and $\overline{\text{RSTB}}$ low. This sets $\overline{\text{EMPTYA}}$, $\overline{\text{EMPTYB}}$, $\overline{\text{FULLA}}$, $\overline{\text{FULLB}}$, and AF/AEB high. Both FIFOs must be reset upon power up.
SAB SBA	1 44	I	Select-control inputs. SAB and SBA select whether real-time or stored data is transferred. A low level selects real-time data and a high level selects stored data. Eight fundamental bus-management functions can be performed as shown in Figure 2.
UNCKA UNCKB	19 26	I	Unload clocks. Data in FIFO A is read to B0–B8 on a low-to-high transition of UNCKB. Data in FIFO B is read to A0–A8 on a low-to-high transition of UNCKB. When the FIFOs are empty, UNCKA and UNCKB have no effect on data residing in memory.

† Terminals listed are for the FN package.

programming procedure for AF/AEA

The almost-full/almost-empty flags (AF/AEA, AF/AEB) are programmed during each reset cycle. The almost-full/almost-empty offset value for FIFO A (X) and for FIFO B (Y) is either a user-defined value or the default values of X = 256 and Y = 256. Below are instructions to program AF/AEA using both methods. AF/AEB is programmed in the same manner for FIFO B.

user-defined X

Take $\overline{\text{DAF}}$ from high to low. This stores A0–A8 as X.

If $\overline{\text{RSTA}}$ is not already low, take $\overline{\text{RSTA}}$ low.

With $\overline{\text{DAF}}$ held low, take $\overline{\text{RSTA}}$ high. This defines AF/AEA using X.

To retain the current offset for the next reset, keep $\overline{\text{DAF}}$ low.

default X

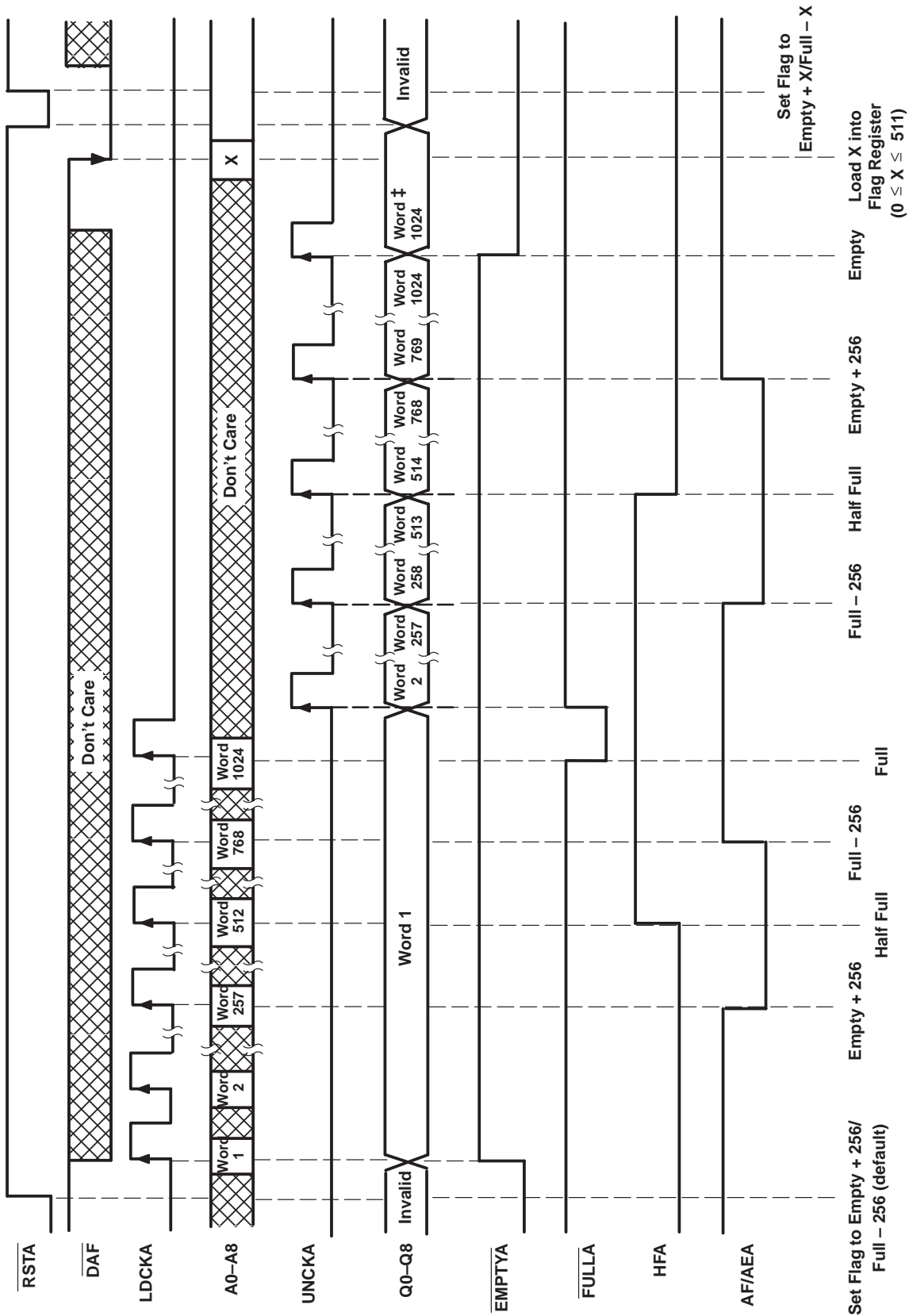
To redefine AF/AE using the default value of X = 256, hold $\overline{\text{DAF}}$ high during the reset cycle.

SN74ACT2235

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SCAS148E – DECEMBER 1990 – REVISED APRIL 1998



† Operation of FIFO B is identical to that of FIFO A.

‡ Last valid data stays on outputs when FIFO goes empty due to a read.

Figure 1. Timing Diagram for FIFO A†

ASYNCHRONOUS BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY

SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

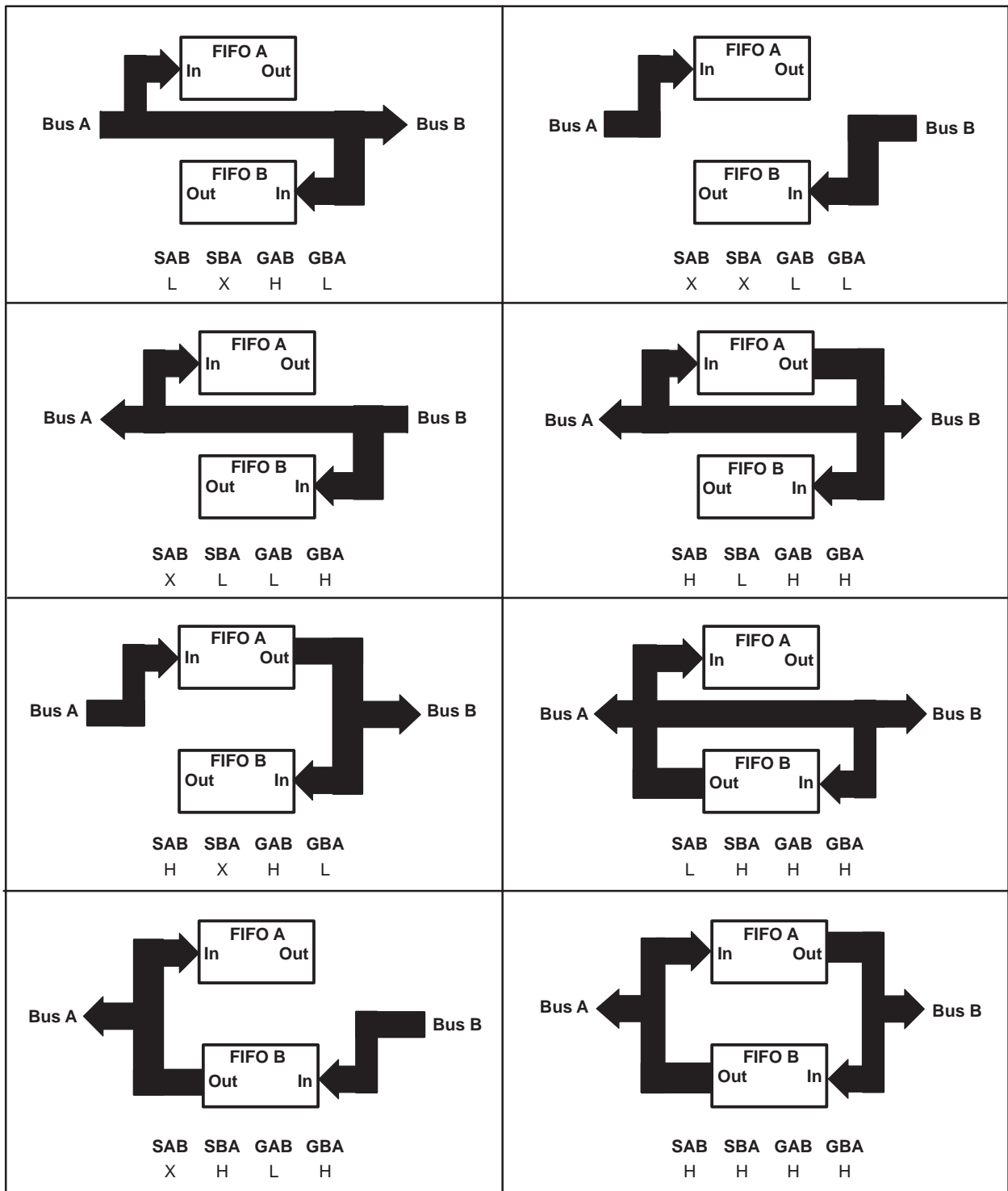


Figure 2. Bus-Management Functions

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SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	$V_{CC} = 4.5\text{ V}$, $I_{OH} = -8\text{ mA}$		2.4			V
V_{OL}	Flags	$V_{CC} = 4.5\text{ V}$, $I_{OL} = 8\text{ mA}$			0.5	V
	I/O ports	$V_{CC} = 4.5\text{ V}$, $I_{OL} = 16\text{ mA}$			0.5	
I_I	$V_{CC} = 5.5\text{ V}$, $V_I = V_{CC}$ or 0				±5	μA
I_{OZ}	$V_{CC} = 5.5\text{ V}$, $V_O = V_{CC}$ or 0				±5	μA
$I_{CC}‡$	$V_I = V_{CC} - 0.2\text{ V}$ or 0		10		400	μA
$\Delta I_{CC}§$	$V_{CC} = 5.5\text{ V}$, One input at 3.4 V, Other inputs at V_{CC} or GND				1	mA
C_i	$V_I = 0$, $f = 1\text{ MHz}$				4	pF
C_o	$V_O = 0$, $f = 1\text{ MHz}$				8	pF

† All typical values are at $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$.

‡ I_{CC} is tested with outputs open.

§ This is the supply current when each input is at one of the specified TTL voltage levels rather than 0 V or V_{CC} .

timing requirements over recommended operating conditions (unless otherwise noted) (see Figure 3)

			'ACT2235-20		'ACT2235-30		'ACT2235-40		'ACT2235-60		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	LDCKA or LDCKB	50		33		25		16.7		MHz
		UNCKA or UNCKB	50		33		25		16.7		
t_w	Pulse duration	$\overline{\text{RSTA}}$ or $\overline{\text{RSTB}}$ low	20		20		25		25		ns
		LDCKA or LDCKB low	8		10		14		20		
		LDCKA or LDCKB high	8		10		14		20		
		UNCKA or UNCKB low	8		10		14		20		
		UNCKA or UNCKB high	8		10		14		20		
		$\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ high	10		10		10		10		
t_{su}	Setup time	Data before LDCKA or LDCKB↑	4		4		5		5		ns
		Define AF/AE: D0–D8 before $\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ ↓	5		5		5		5		
		Define AF/AE: $\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ ↓ before $\overline{\text{RSTA}}$ or $\overline{\text{RSTB}}$ ↑	7		7		7		7		
		Define AF/AE (default): $\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ high before $\overline{\text{RSTA}}$ or $\overline{\text{RSTB}}$ ↑	5		5		5		5		
		$\overline{\text{RSTA}}$ or $\overline{\text{RSTB}}$ inactive (high) before LDCKA or LDCKB↑	5		5		5		5		
t_h	Hold time	Data after LDCKA or LDCKB↑	1		1		2		2		ns
		Define AF/AE: D0–D8 after $\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ ↓	0		0		0		0		
		Define AF/AE: $\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ low after $\overline{\text{RSTA}}$ or $\overline{\text{RSTB}}$ ↑	0		0		0		0		
		Define AF/AE (default): $\overline{\text{DAF}}$ or $\overline{\text{DBF}}$ high after $\overline{\text{RSTA}}$ or $\overline{\text{RSTB}}$ ↑	0		0		0		0		

SN74ACT2235

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SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50$ pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	'ACT2235-20			'ACT2235-30		'ACT2235-40		'ACT2235-60		UNIT
			MIN	TYP†	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}	LDCK		50			33		25		16.7	MHz	
	UNCK		50			33		25		16.7		
t _{pd}	LDCK↑, LDCKB↑	B or A	8		22	8	22	8	24	8	26	ns
	UNCKA↑, UNCKB↑		12	17	25	12	25	12	35	12	45	
t _{PLH}	LDCK↑, LDCKB↑	EMPTYA, EMPTYB	4		15	4	15	4	17	4	19	ns
t _{PHL}	UNCKA↑, UNCKB↑	EMPTYA, EMPTYB	2		17	2	17	2	19	2	21	ns
	RSTA↓, RSTB↓		2		18	2	18	2	20	2	22	
	LDCK↑, LDCKB↑	FULLA, FULLB	4		15	4	15	4	17	4	19	
t _{PLH}	UNCKA↑, UNCKB↑	FULLA, FULLB	4		15	4	15	4	17	4	19	ns
	RSTA↓, RSTB↓	FULLA, FULLB	2		15	2	15	2	17	2	19	
	RSTA↓, RSTB↓	AF/AEA, AF/AEB	2		15	2	15	2	17	2	19	
	LDCK↑, LDCKB↑	HFA, HFB	2		15	2	15	2	17	2	19	
t _{PHL}	UNCKA↑, UNCKB↑	HFA, HFB	4		18	4	18	4	20	4	22	ns
	RSTA↓, RSTB↓		1		15	1	15	1	17	1	19	
t _{pd}	SAB or SBA‡	B or A	1		11	1	11	1	12	1	14	ns
	A or B		1		11	1	11	1	12	1	14	
	LDCK↑, LDCKB↑	AF/AEA, AF/AEB	2		18	2	18	2	20	2	22	
	UNCKA↑, UNCKB↑		2		18	2	18	2	20	2	22	
t _{en}	GBA or GAB	A or B	2		11	2	11	2	13	2	15	ns
t _{dis}	GBA or GAB	A or B	1		9	1	9	1	11	1	13	ns

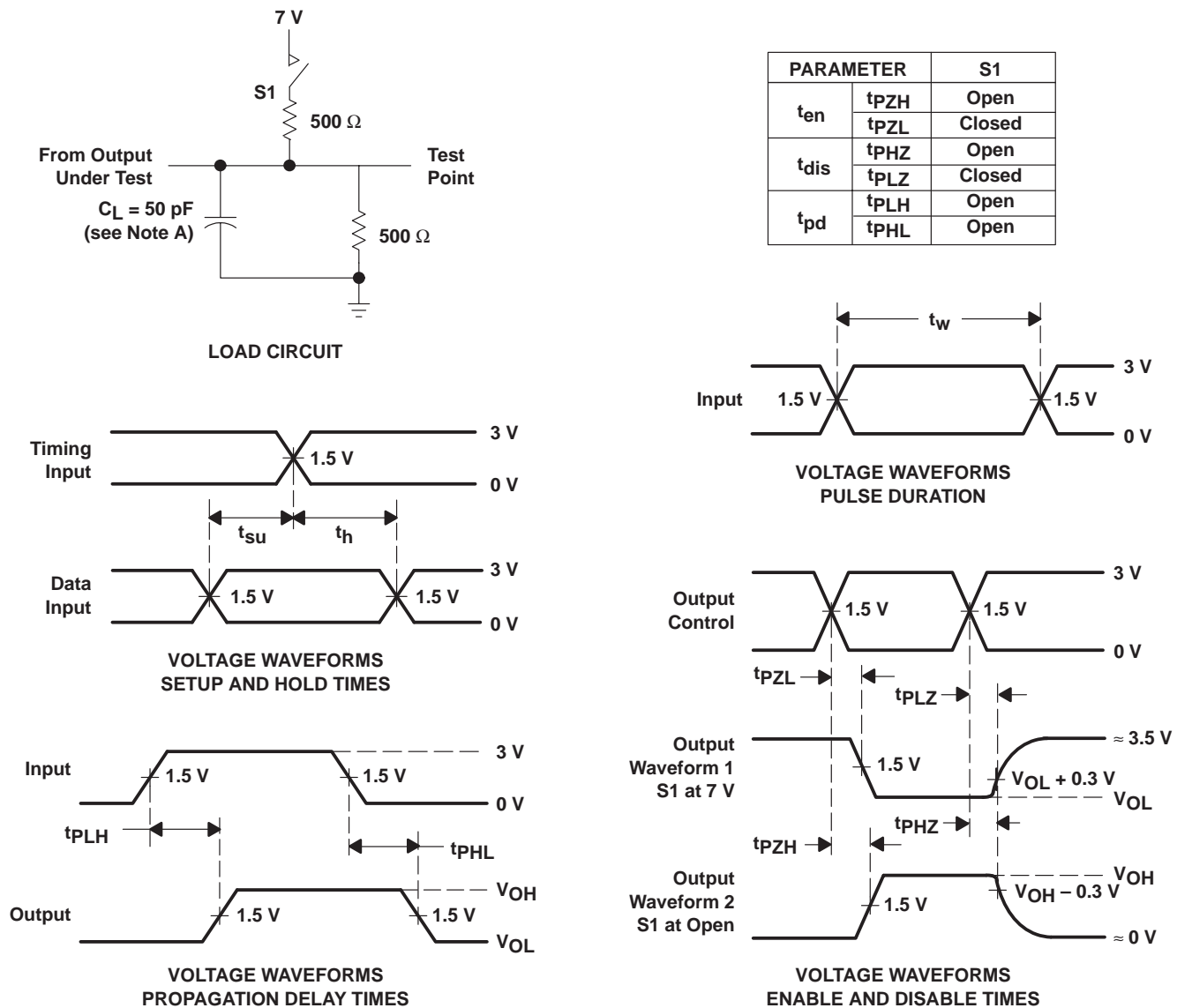
† All typical values are at $V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$.

‡ These parameters are measured with the internal output state of the storage register opposite that of the bus input.

operating characteristics, $V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance per 1K bits	Outputs enabled	71	pF
		Outputs disabled	57	

PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes probe and jig capacitance.

Figure 3. Load Circuit and Voltage Waveforms

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SCAS148E – DECEMBER 1990 – REVISED APRIL 1998

TYPICAL CHARACTERISTICS

PROPAGATION DELAY TIME
vs
LOAD CAPACITANCE

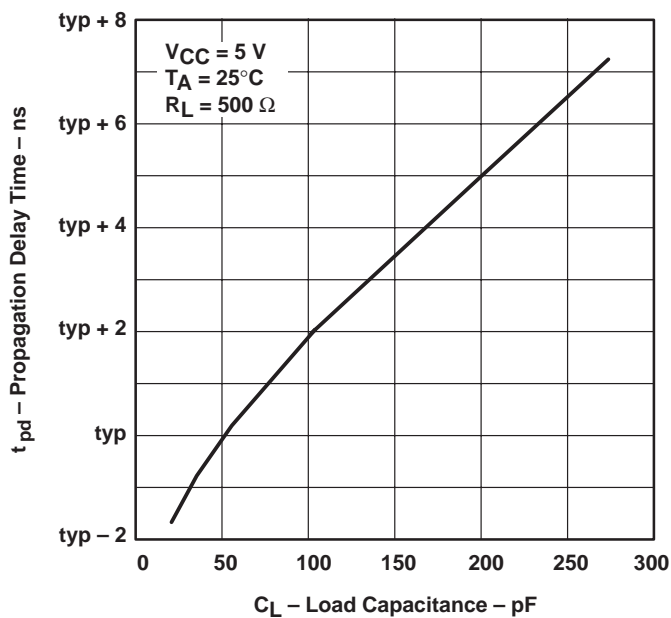


Figure 4

POWER-DISSIPATION CAPACITANCE
vs
SUPPLY VOLTAGE

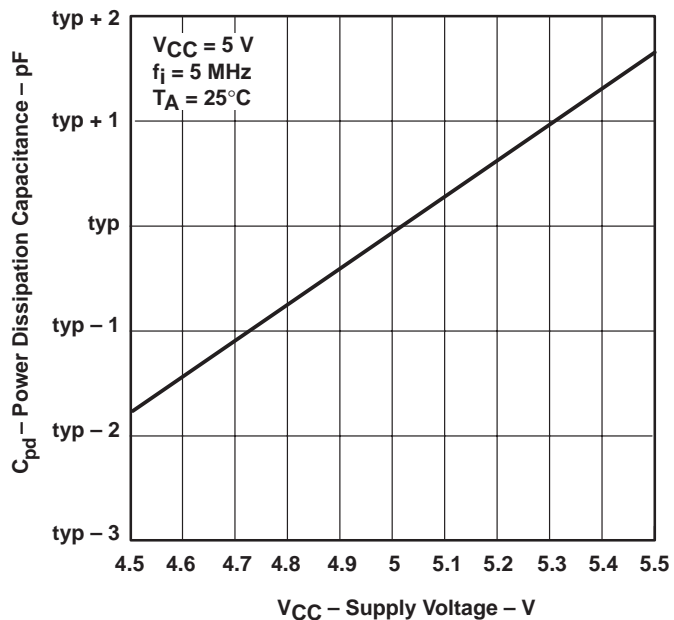


Figure 5

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